

a) placing a [CdS/CdTe] CdS/CdTe device into a chamber and evacuating said chamber to create a vacuum of $\sim 1e-5$ torr;

b) orientating the polycrystalline p-CdTe side of the CdS/CdTe device to face apparatus capable of generating Ar atoms and ions of preferred energy and directionality;

c) introducing Argon and igniting [the] an area of said apparatus to generate Ar atoms and ions of preferred energy and directionality in a range of $\sim 50 - 2000eV$ in a manner so that during ion exposure, the source-to-substrate distance is maintained such that it is less than the mean-free path or diffusion length of the Ar atoms and ions at [the] said vacuum [pressure]; and

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d) allowing exposure of the polycrystalline p-CdTe side [of the layer] to said ion beam for a period less than about [5 minutes] 1 minute to alter the surface stoichiometry from Cd-rich to Te-rich prior to forming a contact interface or semiconductor layer.

E2
20.4.
(Amended) The process of claim [3] 1 wherein said mean-free path of Ar atoms and ions are $>500mm$ [and pressure of the vacuum is about $1e-5$ torr].

REMARKS

The Official Action and cited references have again been carefully reviewed. The review indicates that the claims,